



<b>Form 1449 (Modified)</b>  <b>Information Disclosure Statement By Applicant</b>  (Use Several Sheets if Necessary)	Atty Docket No. NOVLP098	Application No.: 10/800,409
	Applicant: Wu et al.	
	Filing Date 03-11-2004	Group 1762

#### U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
BC	A1	6,797,643 B2	09.2004	Rocha-Alvarez et al.			
	A2	6,815,373 B2	11.2004	Singh et al.			
	A3	6,914,014 B2	07.2005	Li et al.			
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	A5	6,258,735 B1	07.2001	Xia et al.			
	A6	6,715,498 B1	04.2004	Humayun et al.			
	A7	5,849,640	12.1998	Hsia et al.			
	A8	6,573,030 B1	06.03.03	Fairbairn et al.			
	A9	2004/0096586 A1	05.2004	Schulberg et al.			
	A10	2003/0198895 A1	10.2003	Toma et al.			
BC	A11	6,846,380 B2	01.2005	Dickinson et al.			

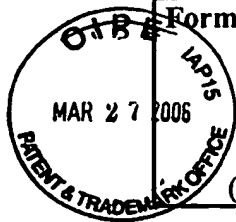
#### Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation	
							Yes	No

#### Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
BC	C1	U.S. Office Action mailed December 27, 2005, from U.S. Application No. 10/789,103 [Atty Dkt No. NOVLP094/NVLS-002919].
	C2	U.S. Office Action mailed February 7, 2006, from U.S. Application No. 10/672,305 [Atty Dkt No. NOVLP069/NVLS-000821].
	C3	U.S. Office Action mailed December 20, 2005, from U.S. Application No. 10/672,311 [Atty Dkt No. NOVLP075/NVLS-000820].
	C4	U.S. Office Action mailed December 20, 2005, from U.S. Application No. 10/849,568 [Atty Dkt No. NOVLP083/NVLS-2867].
	C5	U.S. Office Action mailed January 9, 2006, from U.S. Application No. 10/785,235 [Atty Dkt No. NOVLP085/NVLS-2875].
	C6	U.S. Office Action mailed February 28, 2006, from U.S. Application No. 10/404,693 [Atty Dkt No. NOVLP064/NVLS-794].
BC	C7	Subramonium et al., "Pulsed PECVD Method for Modulating Hydrogen Content in Hard Mask", U.S. Application No. 11/318,269, filed December 23, 2005 (Atty Dkt: NOVLP144/NVLS-3102)
Examiner		Date Considered
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	B	6,383,955	5/7/02	Matsuki, et al.	438	790	6/7/99
BC	C						
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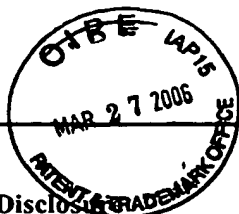
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Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
BC	K	Jan, C.H., et al, <i>90NM Generation, 300mm Wafer Low k ILD/Cu Interconnect Technology</i> , 2003 IEEE Interconnect Technology Conference.
BC	L	U.S. Application No. 10/820,525 (Atty Docket No.: NOVLP091), entitled: METHODS FOR PRODUCING LOW-K CDO FILMS WITH LOW RESIDUAL STRESS, Wu et al.
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	A3	6,365,266	04.02.02	MacDougall et al.			
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Examiner /Bret Chen/				Date Considered 06/11/2006			

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Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
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	C2	Yung et al., "Spin-on Mesoporous Silica Films with Ultralow Dielectric Constants, Ordered Pore Structures, and Hydrophobic Surfaces," Adv. Mater. 2001, 13, No. 14, 1099-1102
	C3	Schulberg et al., "System for Deposition of Mesoporous Materials," U.S. Patent Application No. 10/295,965, filed November 15, 2002, 64 Pages
	C4	Watkins et al., "Mesoporous Materials and Methods," U.S. Patent Application No. 10/301,013, filed November 21, 2002, 34 Pages
	C5	Justin F. Gaynor, "In-Situ Treatment of Low-K Films With a Silylating Agent After Exposure To Oxidizing Environments," U.S. Patent Application No. 10/056,926 filed January 24, 2002, 34 Pages
	C6	Humayun et al., "Method for Forming Porous Films By Porogen Removal Combined With In SITU Surface Modification", Novellus Corporation, Application No. 10/404,693, filed 3/31/03, pages 1-32. Atty. Docket No. NOVLP064/NVLS-0007
	C7	Tipton et al., "Method Of Porogen Removal From Porous Low-K Films Using UV Radiation", Novellus Systems, Inc., Application No. 10/672,311, filed 9/26/03, pages 1-27. Atty. Docket No. NOVLP075/NVLS-000820
	C8	U.S. Patent Application No. 10/016,017, File Date: December 12, 2001 (Atty Dkt: NOVLP030)
	C9	U.S. Patent Application No. 10/125,614, File Date: April 18, 2002 (Atty Dkt: NOVLP028)
	C10	U.S. Patent Application No. 10/202,987, File Date: July 23, 2002 (Atty Dkt: NOVLP028X1)
	C11	Tipton et al., "Method for Removal of Porogens From Porous Low-K Films Using Supercritical Fluids", Novellus Systems, Inc., Application No. 10/672,305, filed 9/26/03, pages 1-32. Atty. Docket No. NOVLP069/NVLS-000821
	C12	Gangpadhyay et al., "The First International Surface Cleaning Workshop," Northeastern University, November 11-14, 2002
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	C15	Humayun et al., "Method For Forming Porous Films By Porogen Removal Combined With In Situ Modification", U.S. Patent No. 10/404,693, filed March 31, 2003, Office Action dated March 15, 2005 (Atty Dkt: NOVLP064)
	C16	Tipton et al., "Method Of Porogen Removal From Porous Low-K Films Using UV Radiation", U.S. Application No. 10/672,311, filed September 26, 2003, Office Action dated September 7, 2004 (Atty Dkt: NOVLP075/NVLS-000820)
	C17	Tipton et al., "Method Of Porogen Removal From Porous Low-K Films Using UV Radiation", U.S. Application No. 10/672,311, filed September 26, 2003, Office Action dated December 28, 2004 (Atty Dkt: NOVLP075/NVLS-000820)
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	C25	Masuda et al. "Highly Ordered Nanochannel-Array Architecture in Anodic Alumina," App. Phys. Lett. 71(19), November 1997, Pages 2770-2772
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	C30	"Shipley Claims Porous Low K Dielectric Breakthrough," Press Release March 17, 2003.
	C31	Jeffrey M. Calvert and Michael K. Gallagher, Semiconductor International, 26 (12), 56 (2003).
	C32	Van Bavel et al., Future Fab International, 16, (2004).
	C33	Caluwaerts et al, "Post Patterning Meso Porosity Creation: A Potential Solution For Pore Sealing," IITC 2003.
	C34	Peter Singer, "New Materials and Designs to Improve Transistor Performance", April 1, 2004, Semiconductor International.
	C35	Ghani et al, "A 90nm High Volume Manufacturing Logic Technology Featuring Novel 45nm Gate Length Strained Silicon CMOS Transistors", IEEE, © 2003.
	C36	Bhadri N. Varadarajan, "Tensile Silicon Nitride – P1264 NESL", C & F Study, August 21, 2003.
	C37	Varadarajan, et al., "Strained Transistor Architecture and Method", Novellus Systems, Inc., Appln No. 10/923,259, filed August 20, 2004, pages 1-24. [Atty Docket No. NOVLP108/NVLS-2933].
	C38	Niu et al., "Methods For Improving The Cracking Resistance Of Low-K Dielectric Materials", U.S. Application No. 10/860,340, filed June 2, 2004, (Atty Dkt: NOVLP099)
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	C40	Niu et al., "Methods For Improving The Cracking Resistance Of Low-K Dielectric Materials", U.S. Application No. 10/860,340, Final Office Action dated June 13, 2005, (Atty Dkt: NOVLP099)
	C41	Wang et al., "Plasma Detemplating And Silanol Capping Of Porous Dielectric Films", U.S. Application No. 10/785,235, filed February 23, 2004 (Atty Dkt: NOVLP085)
	C42	Varadarajan et al., "Tensile Dielectric Films Using UV Curing", U.S. Application No. 10/972,084, filed October 22, 2004 (Atty Dkt: NOVLP122)
BC	C43	Fox et al., "Method For Improving Mechanical Properties Of Low Dielectric Constant Materials", U.S. Application No. 10/849,568, filed May 18, 2004 (Atty Dkt: NOVLP083)
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Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
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	C45	Van Den Hoek et al., "VLSI Fabrication Processes For Introducing Pores Into Dielectric Materials," U.S. Application No. 11/050,621, filed January 31, 2005 (Atty Dkt: NOVLP100)
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	C48	Wu et al., "Methods For Improving Integration Performance Of Low Stress CDO Films", U.S. Application No. 10/941,502, filed September 14, 2004 (Atty Dkt: NOVLP107)
	C49	Cho et al., "Methods of Improving Porogen Removal and Film Mechanical Strength in Producing Ultra Low-K Carbon Doped Oxide Films Using Radical Photopolymerization", U.S. Application No. 10/982,654, filed November 5, 2004 (Atty Dkt: NOVLP115)
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BC		
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BC							

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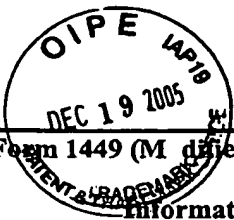
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BC	C1	Cho et al., "Method for Porogen Removal and Mechanical Strength Enhancement of Low-K Carbon Doped Silicon Oxide Using Low Thermal Budget Microwave Curing", U.S. Application No. 11/280,113, filed November 15, 2005 (Atty Dkt: NOVLP145/NVLS-3106)
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